

Amendments to the Specification:

Please replace the paragraph [0027] beginning at page 8, line 14, with the following rewritten paragraph:

-- As previously stated, the semiconductor structure 100 may be used as a component of a MEMS device. As an example, the semiconductor structure 100 may be configured as a movable member ("mover") or a stationary member ("stator") of an electrostatic actuator that is described in a simultaneously filed U.S. patent application Ser. No. ~~10/664,947-XX/XXX,XXX~~ entitled "Stepping Electrostatic Comb Drive Actuator", which is assigned to the same assignee of this disclosure, and is specifically incorporated by reference herein. A portion of a similar electrostatic actuator 500 is illustrated in Fig. 5. The electrostatic actuator 500 includes a movable semiconductor structure ("mover") 502 and a stationary semiconductor structure ("stator") 504. The portion of the movable semiconductor structure 502 shown includes a mover finger 506, while the portion of the stationary semiconductor structure 504 shown includes two stator fingers 508. Typically, the movable and stationary semiconductor structures 502 and 504 include many additional interdigitated mover and stator fingers, respectively. Similar to the semiconductor structure 100, each of the mover and stator fingers 506 and 508 has electrically isolated electrodes 510 and interconnects 518, which are connected to selected areas of the electrodes. In addition, each of the mover and stator fingers 506 and 508 includes a first insulating layer 514, which is located below the interconnects 518, and a second insulating layer (not shown), which is located between the interconnects 518 and the electrodes 510. Although, the mover finger 506 is shown to have five electrodes 510 and each stator finger 508 is shown to have three electrodes 510, the mover and stator fingers typically have many more electrodes. The mover and stator fingers 506 and 508 are interdigitated such that the electrodes 510 on the sides the mover finger oppose the electrodes 510 on the sides of the stator fingers. Many movable and stationary semiconductor structures 502 and 504 may be fabricated from a single silicon wafer by a wafer fabrication process similar to the fabrication process of the semiconductor structure 100, as described above.--